

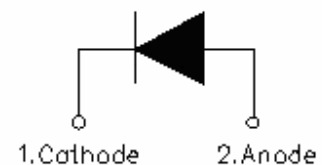
## SDUR6060W ULTRAFAST PLASTIC RECTIFIER

### Applications:

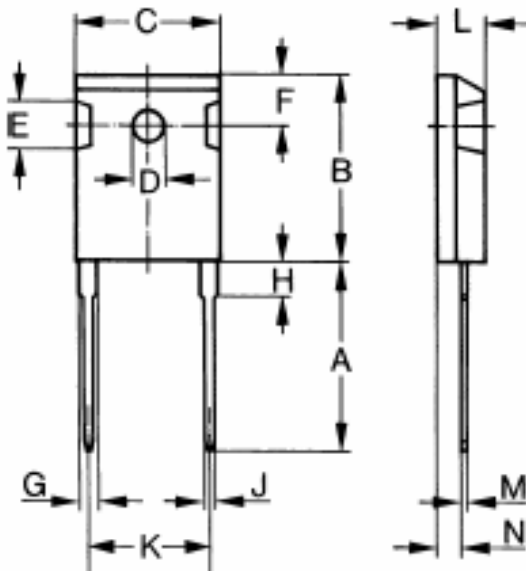
- Switching Power Supply
- Power Switching Circuits
- General Purpose

### Features:

- Ultra-Fast Switching
- High Current Capability
- Low Reverse Leakage Current
- High Surge Current Capability
- Plastic Material has UL Flammability Classification 94V-0
- This is a Pb - Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



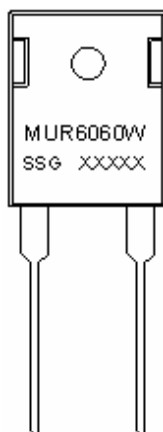
### Mechanical Dimensions: In mm / Inches



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	2.2	2.54	0.087	0.102

**TO-247AC**

**Marking Diagram:**



Where XXXXX is YYWWL

MUR = Device Type  
60 = Forward Current (60A)  
60 = Reverse Voltage (600V)  
W = Configuration  
SSG = SSG  
YY = Year  
WW = Week  
L = Lot Number

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

**Ordering Information:**

Device	Package	Shipping
MUR6060W	TO-247AC (Pb-Free)	30 pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

**Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	600	V
Max. Average Forward	$I_{F(AV)}$	50% duty cycle @ $T_c=75^\circ\text{C}$ , rectangular wave form	60	A
Max. Peak One Cycle Non-Repetitive Surge Current (Per leg)	$I_{FSM}$	8.3ms, Half Sine pulse	600	A

**Electrical Characteristics:**

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop*	$V_{F1}$	@ 70A, Pulse, $T_J = 25^\circ\text{C}$	1.8	V
	$V_{F2}$	@ 70A, Pulse, $T_J = 125^\circ\text{C}$	1.6	V
Max. Reverse Current*	$I_{R1}$	@ $V_R = \text{rated } V_R$ $T_J = 25^\circ\text{C}$	200	$\mu\text{A}$
	$I_{R2}$	@ $V_R = \text{rated } V_R$ $T_J = 125^\circ\text{C}$	14	mA
Max. Reverse Recovery Time	$t_{rr}$	$I_F=500\text{mA}$ , $I_R=1\text{A}$ , and $I_{rm}=250\text{mA}$	50	ns

\* Pulse width < 300  $\mu\text{s}$ , duty cycle < 2%

**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	$T_J$	-	-55 to +150	$^\circ\text{C}$
Max. Storage Temperature	$T_{stg}$	-	-55 to +150	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	0.75	$^\circ\text{C/W}$
Maximum Thermal Resistance Junction to Ambient	$R_{\theta JA}$	DC operation	35	$^\circ\text{C/W}$
Approximate Weight	wt	-	6	g
Case Style	TO-247AC			

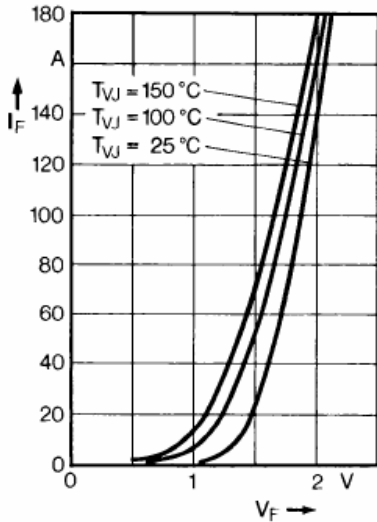


Fig. 1 Forward current versus voltage drop.

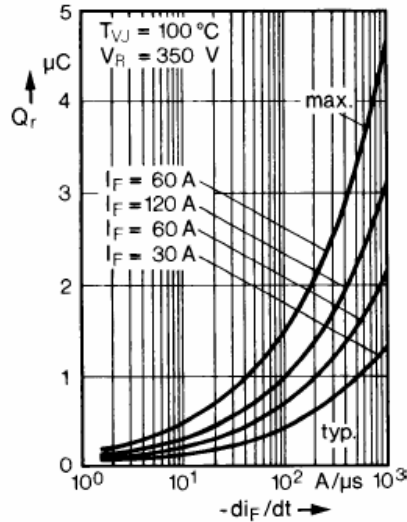


Fig. 2 Recovery charge versus  $-di_F/dt$ .

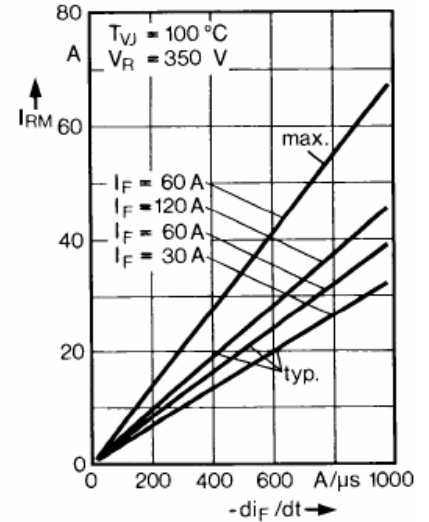


Fig. 3 Peak reverse current versus  $-di_F/dt$ .

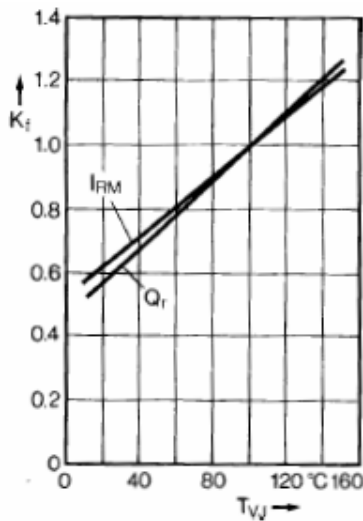


Fig. 4 Dynamic parameters versus junction temperature.

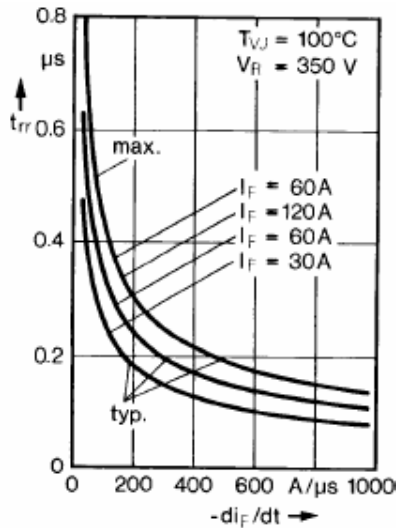


Fig. 5 Recovery time versus  $-di_F/dt$ .

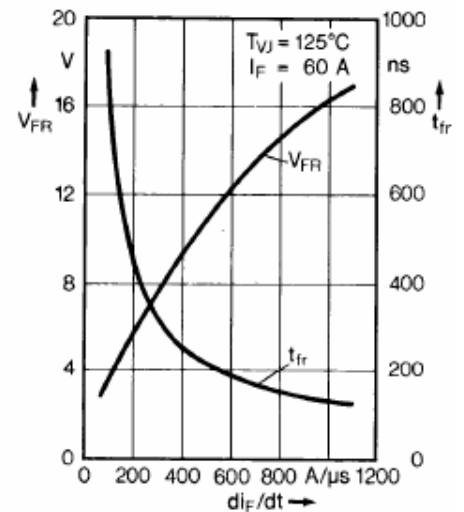


Fig. 6 Peak forward voltage versus  $di_F/dt$ .

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